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Dr. Hiramoto is a member of IEEE, IEICE, and Japan Society of Applied Physics. He was an Elected AdCom Member of IEEE Electron Devices Society in 2001 - 2006. He served as the General Chair of Silicon Nanoelectronics Workshop in 2003 and the Program Chair in 1997, 1999, and 2001. He has served on Program Committee of Symposium on VLSI Technology since 2001. He also served on Program Subcommittee on Integrated Circuits of IEEE International Electron Devices Meeting (IEDM) in 1993, 1994 and Program Subcommittee on CMOS Devices of IEDM in 2003, 2004. He was the Subcommittee Chair of CMOS Devices of IEDM in 2005 and is the Asian Arrangement Co-Chair of IEDM in 2006 and 2007.



photo of Toshiro Hiramoto